

MICROSTRIP/STRIPLINE NIP DIODE SWITCH

DESCRIPTION:

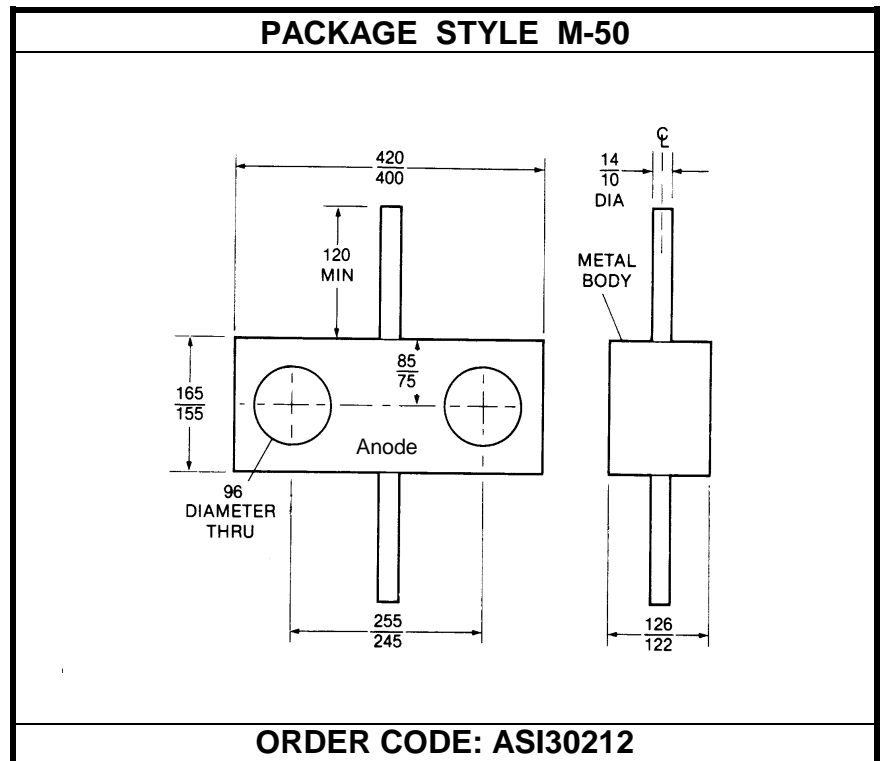
The **ASI 5082-3140** is a Silicon NIP Diode Module Designed for Reflective Attenuator and Switching Applications from 1 GHz to 18 GHz.

FEATURES INCLUDE:

- Direct replacement for **HP 5082-3140**
- Isolation = 20 dB min. at 10 GHz
- Hermetic Package

MAXIMUM RATINGS

I_F	250 mA
V_R	150 V
P_{DISS}	1.75 W @ T _C = 25 °C
T_J	-65 °C to +150 °C
T_{STG}	-65 °C to +150 °C
θ_{JC}	72 °C/W


CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS			MINIMUM	TYPICAL	MAXIMUM	UNITS
V_{BR}	I _R = 10 μA			150			V
V_F	I _F = 100 mA					1.0	V
τ	I _F = 50 mA	I _R = 250 mA			400		μS
I_L	I _F = 0 mA	P _{IN} = 0 dBm	f = 10 GHz			0.5	dB
I_L	I _F = 100 mA	P _{IN} = 0 dBm	f = 10 GHz	20			dB
V_{SWR}	I _F = 0 mA	P _{IN} = 0 dBm	f = 10 GHz			1.5:1	---